



#### N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	Rds(on) max	I <sub>D MAX</sub> T <sub>A</sub> = +25°C
50V	2.0Ω @ V <sub>GS</sub> = 5.0V	300mA
	2.5Ω @ V <sub>GS</sub> = 2.5V	200mA

#### **Features and Benefits**

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V Max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Load Switches
- Level Switches

#### **Mechanical Data**

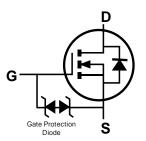
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe.
   Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

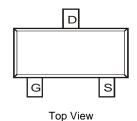




SOT23

Top View





**Equivalent Circuit** 

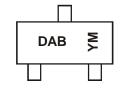
#### **Ordering Information (Note 5)**

Part Number	Case	Packaging
DMN5L06KQ-7	SOT23	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



DAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Key

Year	2006	~	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	T	~	G	Н		J	K	L	М	N	0	Р
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		0	^	4		_	7	0	0		N.I.	7



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Charact	eristic	Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	50	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Drain Current (Note 6)	Continuous Pulsed (Note 7)	I <sub>D</sub>	300 800	mA
Maximum Body Diode Forward Cu	rrent (Note 6)	Is	300	mA

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	$P_{D}$	350	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

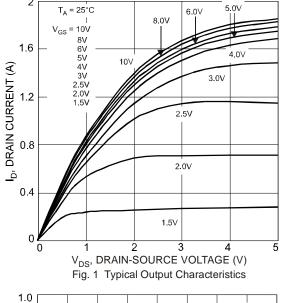
# **Electrical Characteristics** (@ $T_A = \pm 25^{\circ}C$ , unless otherwise specified.)

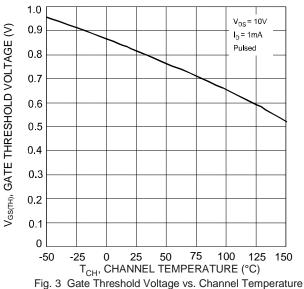
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current @ T <sub>C</sub> = +25°C	C I <sub>DSS</sub>	_	_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$
				1	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$
Gate-Body Leakage	I <sub>GSS</sub>	_	_	500	nA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$
				50	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.49	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
		_	2.0	3.0		$V_{GS} = 1.8V, I_D = 50mA$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	1.6	2.5	Ω	$V_{GS} = 2.5V, I_D = 50mA$
		_	1.3	2.0		$V_{GS} = 5.0V, I_D = 50mA$
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	Y <sub>fs</sub>	200	_	_	mS	$V_{DS} = 10V, I_{D} = 0.2A$
Source-Drain Diode Forward Voltage	$V_{SD}$	0.5	0.8	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C <sub>iss</sub>	_	_	50	pF	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance		_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ -f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	_	5.0	pF	1 = 1.0IVII IZ

Notes:

- 6. Device mounted on FR-4 PCB.
- 7. Pulse width ≤10ms, Duty Cycle ≤1%.
- S. Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.







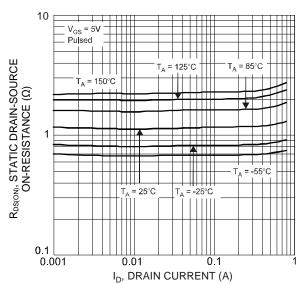
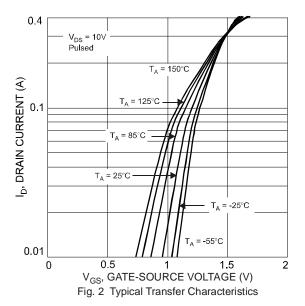


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



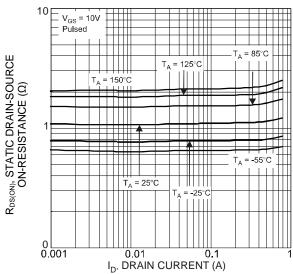


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

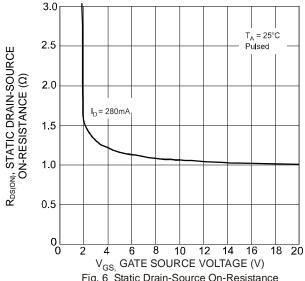


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage



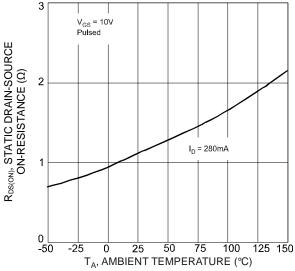


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

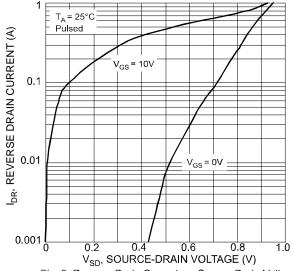
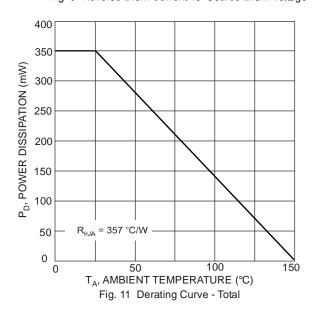


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



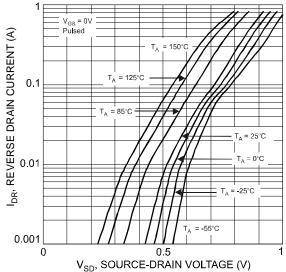


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

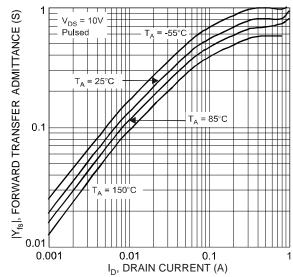
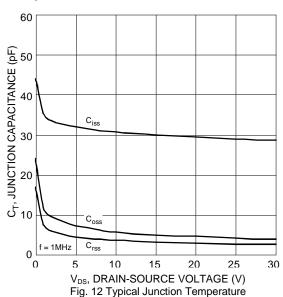


Fig.10 Forward Transfer Admittance vs. Drain Current

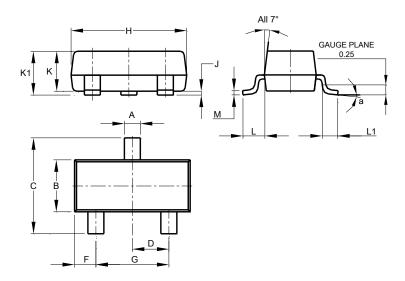




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23

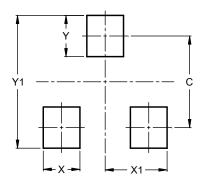


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
C	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Η	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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